

A detailed cross-sectional view of a semiconductor device. The structure consists of several layers and regions. At the bottom is a thick substrate labeled 1. Above it is a layer labeled 2. A region labeled 8 is located within layer 2. Above layer 2 is a layer labeled 3, which contains a region labeled 9b. Above layer 3 is a layer labeled 4, which contains a region labeled 9a. Above layer 4 is a layer labeled 5, which contains a region labeled 10. Within layer 5, there are two regions labeled 5a and 5b, both containing the label N^+ . Above layer 5 is a layer labeled 6, which contains a region labeled 6. Above layer 6 is a layer labeled 7, which contains a region labeled 7a. Above layer 7 is a layer labeled 11. Above layer 11 is a layer labeled 12, which contains a region labeled 12a. Above layer 12 is a layer labeled 13. Above layer 13 is a layer labeled 14. Above layer 14 is a layer labeled 15. Above layer 15 is a layer labeled 16. Above layer 16 is a layer labeled 17. The region between layer 5 and layer 11 is labeled P-WELL. The region between layer 11 and layer 17 is labeled P^{--} .

[illegible]

Fig. 2

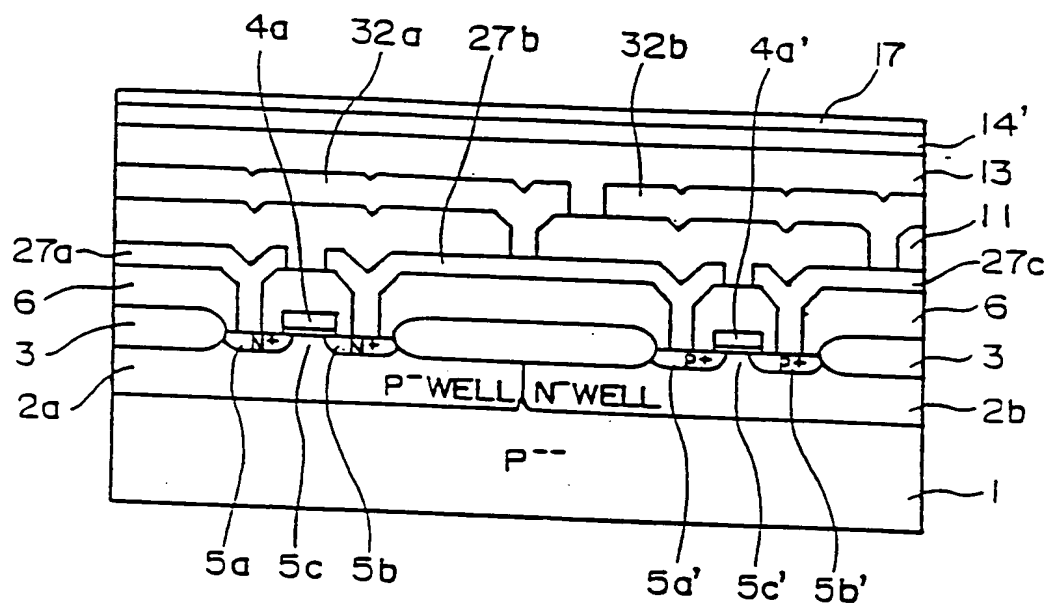


Fig. 4(a)

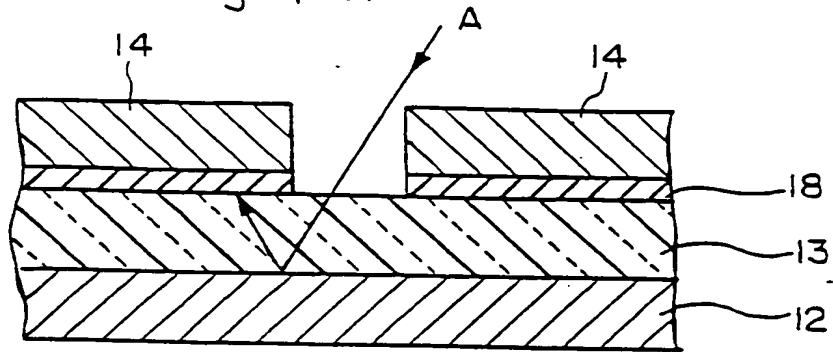


Fig. 4(b)

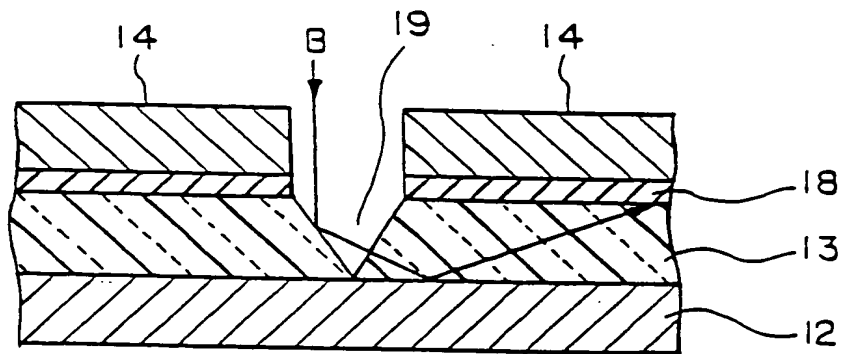


Fig. 4(c)

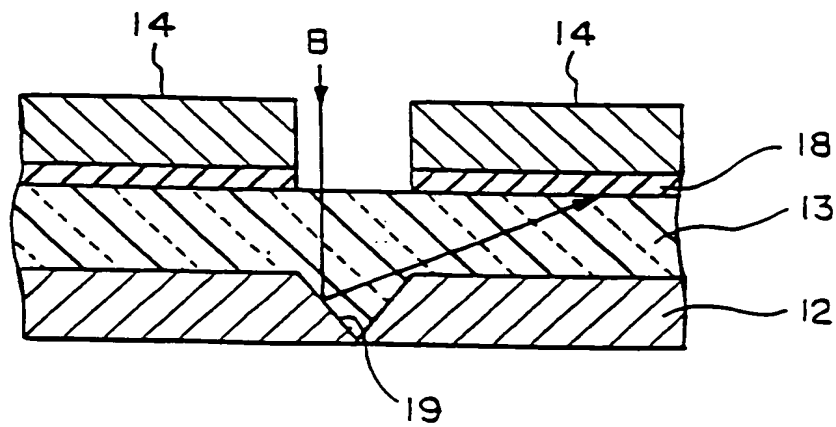


Fig. 5

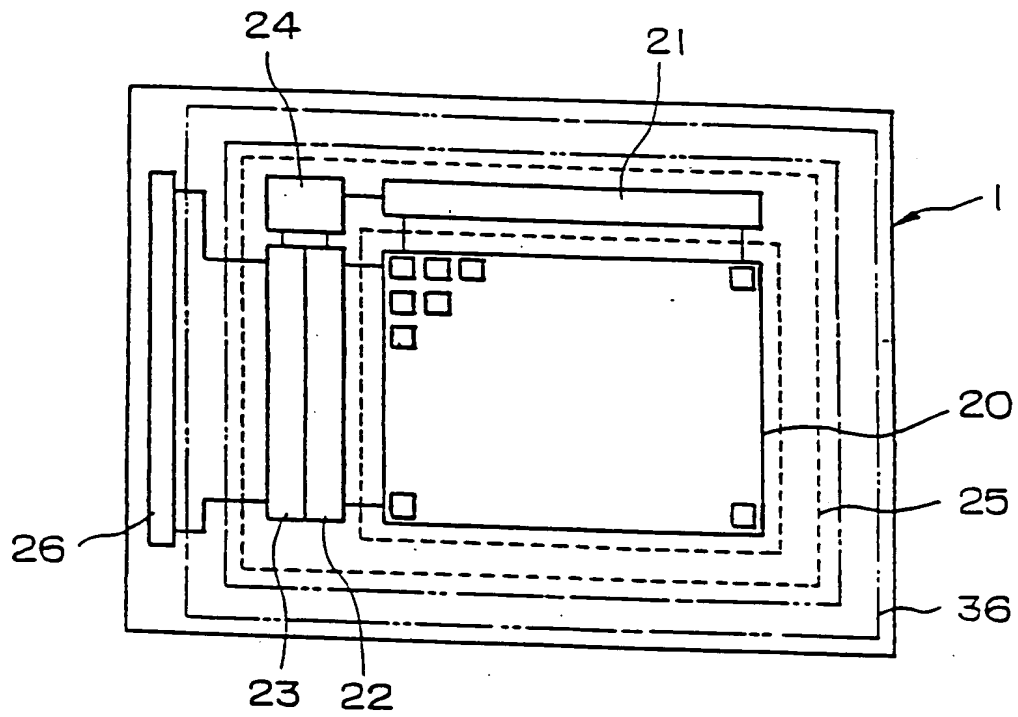


Fig. 6

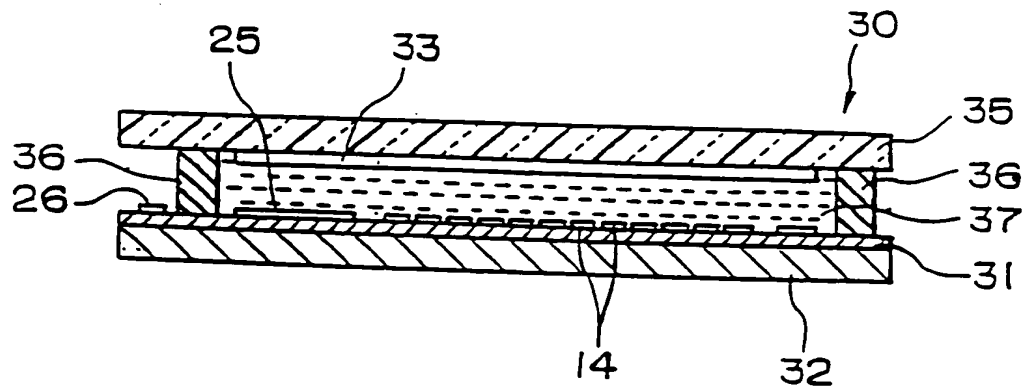


Fig. 7

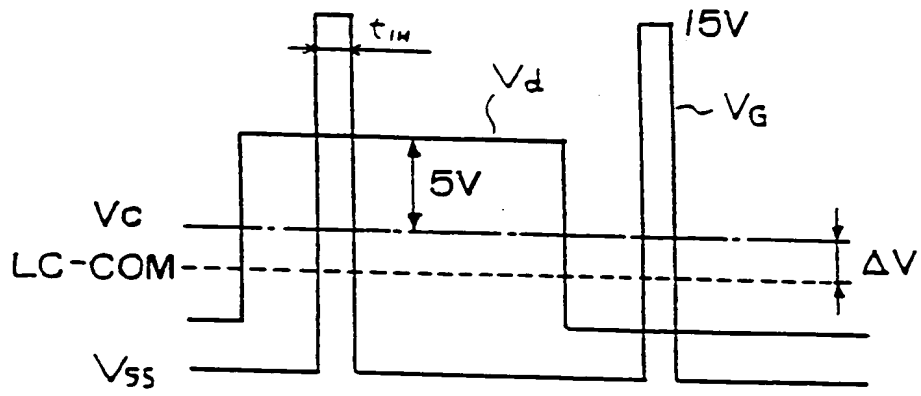


Fig. 8

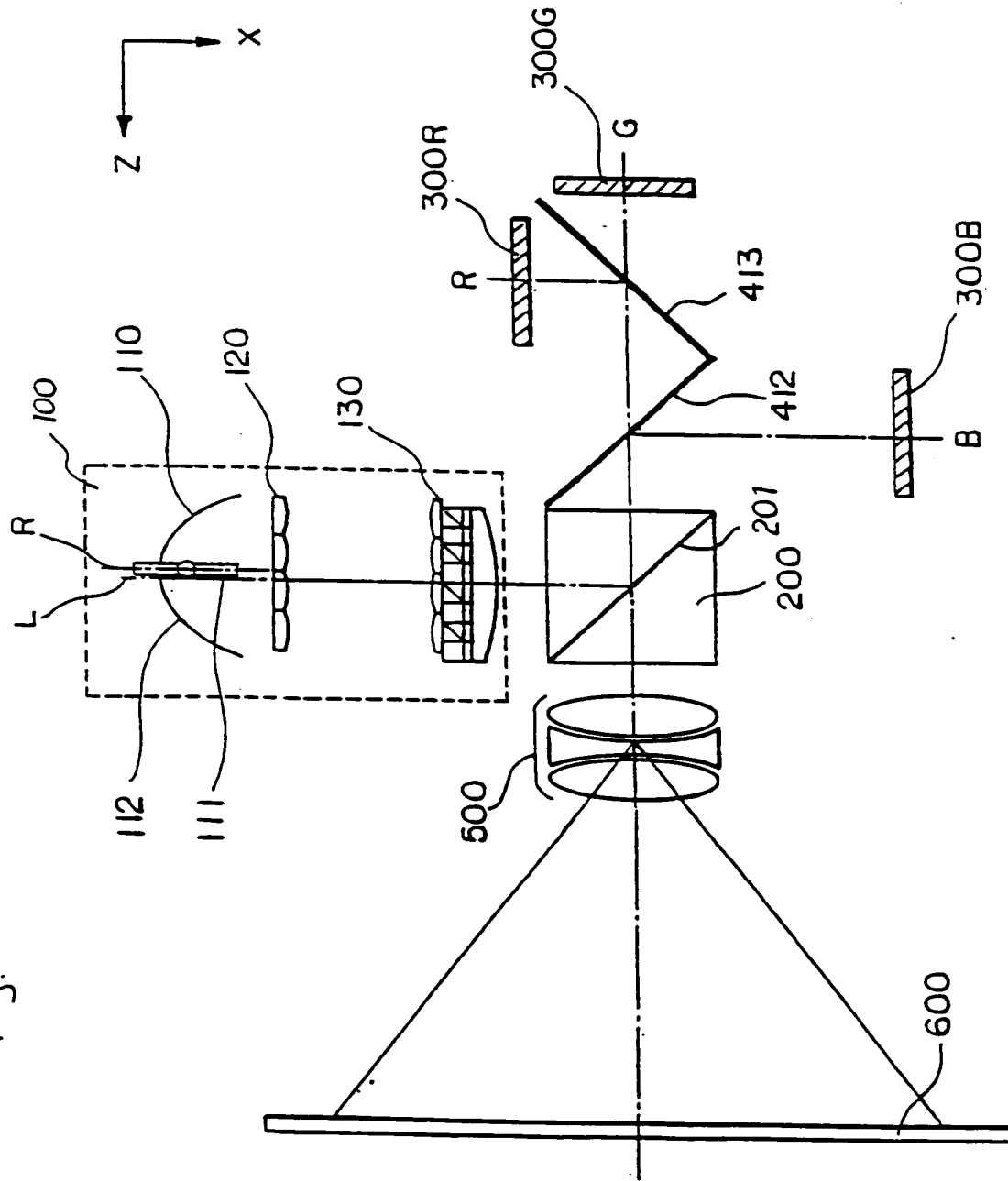


Fig. 9 (a)

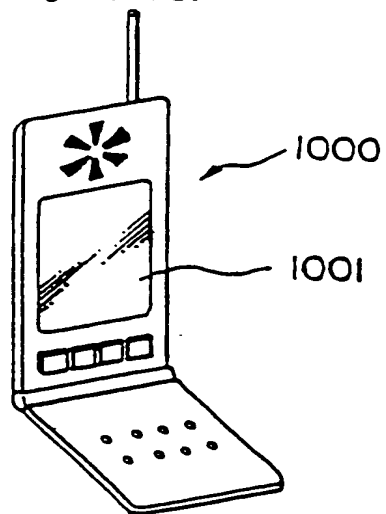


Fig. 9 (b)

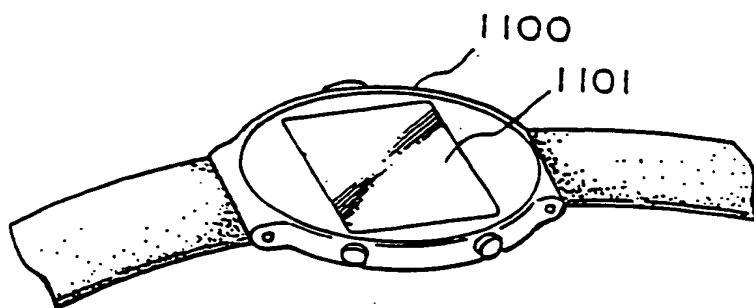


Fig. 9 (c)

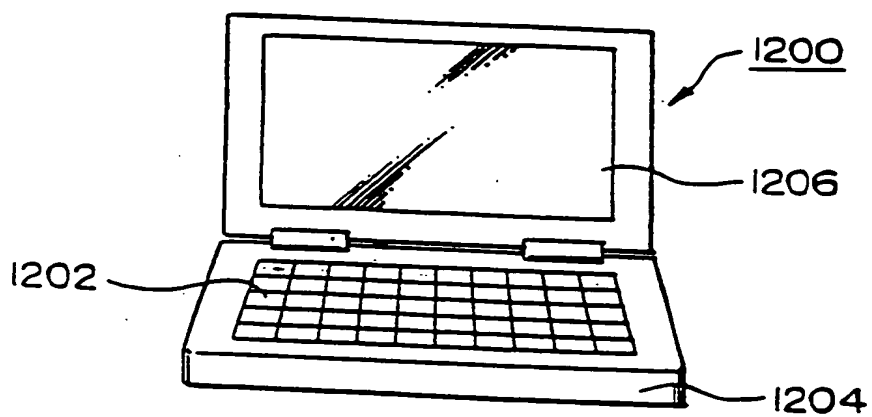


Fig. 10

